

NCE N-Channel Super Trench Power MOSFET

Description

The series of devices uses Super Trench technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS}(\text{ON})}$ and $Q_{\text{g}}.$ This device is ideal for high-frequency switching and synchronous rectification.

Application

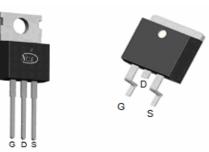
- ●DC/DC Converter
- ●Ideal for high-frequency switching and synchronous rectification

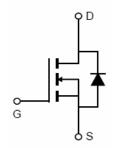
General Features

- ●V_{DS} =150V,I_D =70A $R_{DS(ON)}$ =13.5m Ω (typical) @ V_{GS} =10V
- ●Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- ●175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% AVds TESTED!







Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP1570	NCEP1570	TO-220			
NCEP1570D	NCEP1570D	TO-263	-	-	-

Absolute Maximum Ratings (T_A=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	150	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I _D	70	А
Drain Current-Continuous(T _C =100 °C)	I _D (100℃)	49	Α
Pulsed Drain Current	I _{DM}	280	Α
Maximum Power Dissipation	P _D	200	W
Derating factor		1.33	W/℃
Single pulse avalanche energy (Note 5)	E _{AS}	672	mJ
Operating Junction and Storage Temperature Range	T_{J} , T_{STG}	-55 To 175	$^{\circ}$ C

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NCEP1570,NCEP1570D

Thermal Characteristic

Thermal Résistance, Junction-to-Case ^(Note 2)	$R_{ heta JC}$	0.75	°C/W	
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Electrical Characteristics (T_A=25°C unless otherwise noted)

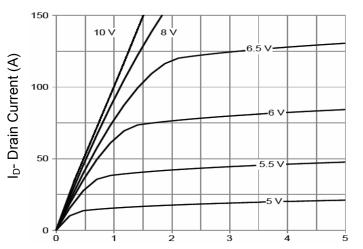
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	150	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =150V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	2.0	3.1	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =35A	-	13.5	15	mΩ
Forward Transconductance	G FS	V _{DS} =5V,I _D =35A	-	58	-	S
Dynamic Characteristics (Note4)			•	•		
Input Capacitance	C _{lss}	\/ -75\/\/ -0\/	-	2000	-	PF
Output Capacitance	Coss	V_{DS} =75V, V_{GS} =0V, F=1.0MHz		280	-	PF
Reverse Transfer Capacitance	C _{rss}			16	-	PF
Switching Characteristics (Note 4)	<u> </u>		•	•		
Turn-on Delay Time	t _{d(on)}		-	12.5	-	nS
Turn-on Rise Time	t _r	V_{DD} =75V, I_{D} =35A	-	3.8	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{G} =3 Ω	-	14	-	nS
Turn-Off Fall Time	t _f		-	3.5	-	nS
Total Gate Charge	Qg	\/ 75\/ 05A	-	35	-	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=75V,I_{D}=35A,$	-	11.8	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =10V	-	9.9	-	nC
Drain-Source Diode Characteristics	-		•			I.
Diode Forward Voltage (Note 3)	V _{SD}	V_{GS} =0 V , I_{S} =35 A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	70	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = 35A	-	105	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$	-	160	-	nC

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec. The value of R_{BJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.
- 3. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- 5. E_{AS} condition : $Tj=25^{\circ}C$, $V_{DD}=50V$, $V_{G}=10V$, L=0.5mH, $Rg=25\Omega$

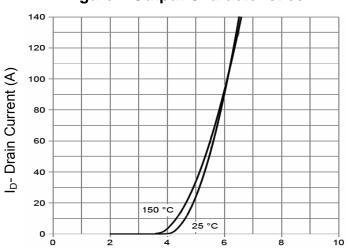


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)

Figure 1 Output Characteristics



Vgs Gate-Source Voltage (V)

Figure 2 Transfer Characteristics

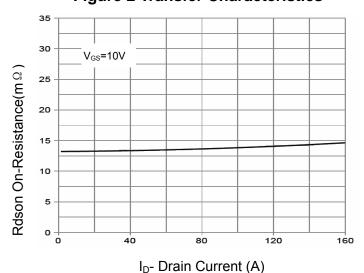
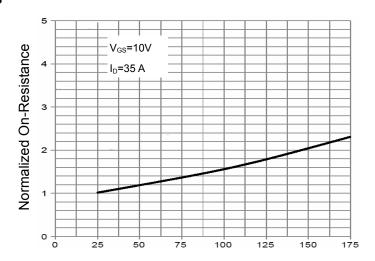


Figure 3 Rdson- Drain Current



T_J-Junction Temperature(°C)

Figure 4 Rdson-Junction Temperature

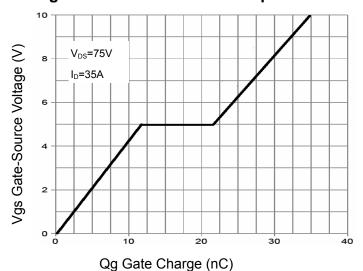
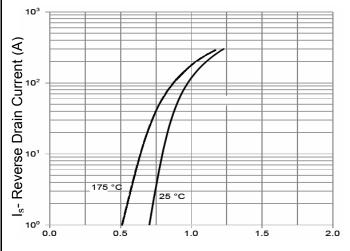


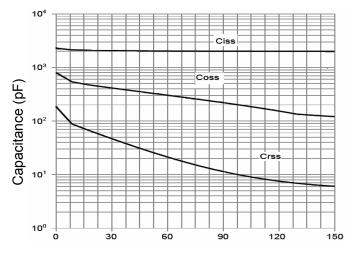
Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

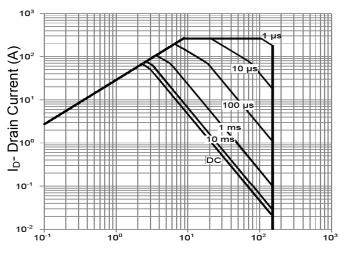
Figure 6 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

Figure 7 Capacitance vs Vds



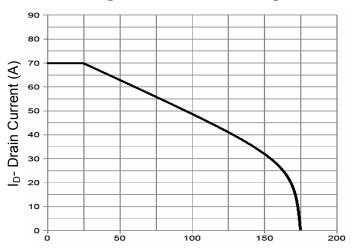
Vds Drain-Source Voltage (V)

Figure 8 Safe Operation Area



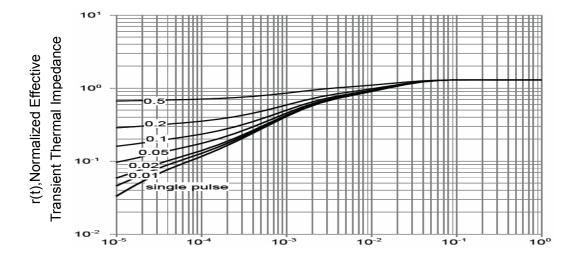
 T_J -Junction Temperature($^{\circ}$ C)

Figure 9 Power De-rating



T_J-Junction Temperature (°C)

Figure 10 Current De-rating

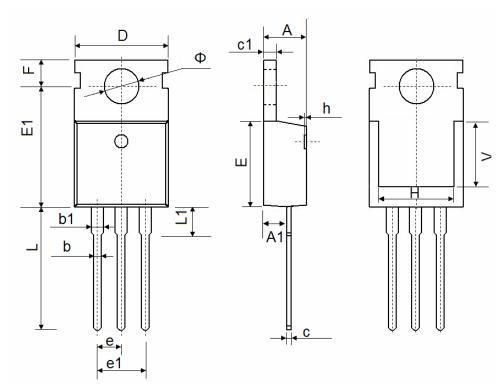


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



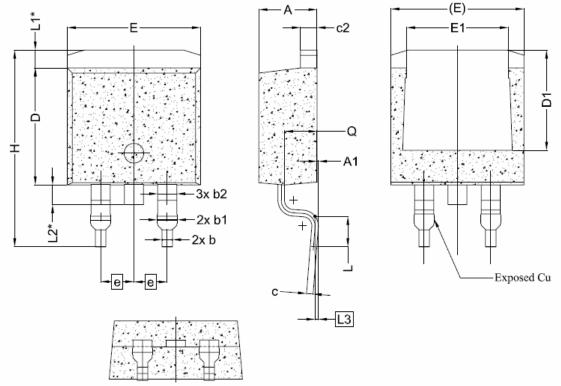
TO-220-3L Package Information



Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900	6.900 REF. 0.276 RE		REF.	
Ф	3.400	3.800	0.134	0.150	



TO-263-2L Package Information



Symbol	Dimensions In Millimeters				
Symbol	Min.	Nom.	Max.		
А	4.24	4.44	4.64		
A1	0.00	0.10	0.25		
b	0.70	0.80	0.90		
b1	1.20	1.55	1.75		
b2	1.20	1.45	1.70		
С	0.40	0.50	0.60		
c2	1.15	1.27	1.40		
D	8.82	8.92	9.02		
D1	6.86 7.65		-		
E	9.96	9.96 10.16			
E1	6.89 7.77		7.89		
е	2.54BSC				
Н	14.61 15.00		15.88		
L	1.78	2.32	2.79		
L1	1.36 REF.				
L2	1.50 REF.				
L3	0.25 BSC				
Q	2.30	2.48	2.70		

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NCEP1570,NCEP1570D

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